

International Rectifier IRFK3D150, IRFK3F150

Isolated Base Power HEX-pak™ Assembly - Half Bridge Configuration

- High Current Capability.
- UL recognised E78996.
- Electrically Isolated Base Plate.
- Easy Assembly into Equipment.

Description

The HEX-pak™ utilises the well-proven HEXFET™ die, combining low on-state resistance with high transconductance. These superior technology die are assembled by state of the art techniques into the TO-240 package, featuring 2.5kV rms isolation and solid M5 screw connections. The small footprint means the package is highly suited to power applications where space is a premium. Available in two versions, IRFK.D... for fast switching and IRFK.F... for oscillation sensitive applications.

$$V_{DS} = 100V$$

$$R_{DS(on)} = 20m\Omega$$

$$I_D = 125A$$

Absolute Maximum Rating

Parameter	Max.	Units
I_D @ $T_C=25^\circ C$ Continuous Drain Current	125	A
I_D @ $T_C=100^\circ C$ Continuous Drain Current	55	A
I_{DM} Pulse Drain Current	435	A ①
P_D @ $T_C=25^\circ C$ Maximum Power Dissipation	625	W
V_{GS} Gate-to-Source Voltage	20	V
V_{INS} R.M.S. Isolation Voltage, circuit to base	2.5	kV
T_J Operating Junction Temperature Range	-40 to 150	$^\circ C$
T_{STG} Storage Temperature Range	-40 to 150	$^\circ C$

Thermal and Mechanical Specifications

Parameter	Min.	Typ.	Max.	Units
R_{thJC} Junction-to-Case	-	-	0.20	K/W ②
R_{thCS} Case-to-Sink, smooth & greased surface	-	0.1	-	K/W
T Mounting Torque +10%				③
HEXpak to Heatsink	-	5	-	Nm
Busbar to HEXpak	-	3	-	Nm ④
wt Approximate Weight	-	140	-	g
	-	5	-	oz

Notes:

- ① - Repetitive Rating: Pulse width limited by maximum junction temperature see figure 8.
- ② - Per Module.
- ③ - A mounting compound is recommended and the torque should be rechecked after a period of three hours to allow for the spread of the compound.

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Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (Unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Test Conditions	
B _{VDS}	Drain-to-Source Breakdown voltage	100	-	-	V	V _{GS} =0V, I _D =1.0mA	
R _{DS(on)}	Static Drain-to-Source On-State Resistance	-	16	20	mΩ	V _{GS} =10V, I _D =45A	
I _{D(on)}	On-State Drain Current	125	-	-	A	V _{DS} > I _{D(on)} × R _{DS(on)} max, V _{GS} =10V	
V _{GS(th)}	Gate Threshold Voltage	2.0	-	4.0	V	V _{DS} =V _{GS} , I _D =1.0mA	
g _{fs}	Forward Transconductance ④	39	60	-	S	V _{DS} > 50V, I _D =55A	
I _{DSS}	Zero Gate Voltage Drain Current	-	-	0.75	mA	V _{DS} =V _{DS} max, V _{GS} =0V	
		-	-	3.0	mA	V _{GS} =10V, T _C =125°C, V _{DS} =V _{DS} max × 0.8	
I _{GSS}	Gate-to-Source Leakage Forward	-	-	300	nA	V _{GS} =20V	
I _{GSS}	Gate-to-Source Leakage Reverse	-	-	-300	nA	V _{GS} =-20V	
Q _g	Total Gate Charge	-	250	390	nC	I _D =125A, V _{GS} =10V,	
Q _{gs}	Gate-to-Source Charge	-	50	80	nC	V _{DS} =V _{DS} max × 0.8	
Q _{gd}	Gate-to-Drain ("Miller") Charge	-	132	195	nC		
t _{d(on)}	Turn-on Delay Time	IRFK3D150	-	65	-	ns	V _{DD} =40V, I _D =55A,
		IRFK3F150	-	75	-	ns	
t _r	Rise Time	IRFK3D150	-	160	-	ns	V _{GS} =10V,
		IRFK3F150	-	200	-	ns	
t _{d(off)}	Turn-off Delay Time	IRFK3D150	-	190	-	ns	R _{SOURCE} =3.3Ω
		IRFK3F150	-	250	-	ns	
t _f	Fall Time	IRFK3D150	-	60	-	ns	
		IRFK3F150	-	100	-	ns	
L _{DS}	Drain-to-Source Inductance	-	18	-	nH		
C _{iss}	Input Capacitance	-	8.0	-	nF	V _{GS} =0V, V _{DS} =25V,	
C _{oss}	Output Capacitance	-	3.0	-	nF	f=1.0MHz	
C _{rss}	Reverse Transfer Capacitance	-	0.8	-	nF		
	Linear Derating Factor	-	-	5	W/K		

Source-Drain Diode Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
I_S	Continuous Source Current (Body Diode)	-	-	125	A	
I_{SM}	Pulsed Source Current (Body Diode)	-	-	435	A	
V_{SD}	Diode Forward Voltage	-	-	2.5	V	$V_{GS}=0V, I_S=125A, T_C=25^\circ\text{C}$
t_{rr}	Reverse Recovery Time	100	210	420	ns	$di/dt=400A/\mu s, T_J=150^\circ\text{C}$
Q_{rr}	Reverse Recovered Charge	3.6	6.9	14.0	μC	$I_S=125A$

Notes:

④ - Pulse Width $\leq 300\mu s$; Duty cycle $\leq 2\%$.



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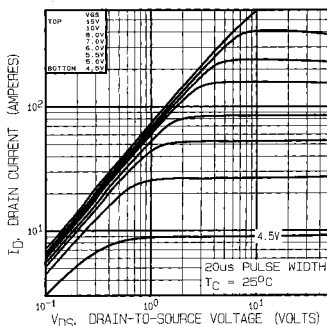


Fig 1. Typical Output Characteristics,
 $T_C = 25^\circ\text{C}$

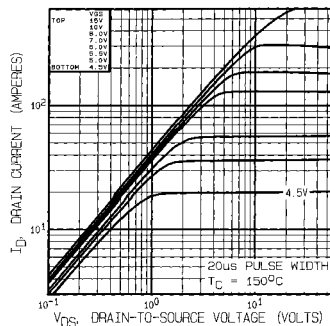


Fig 2. Typical Output Characteristics,
 $T_C = 150^\circ\text{C}$

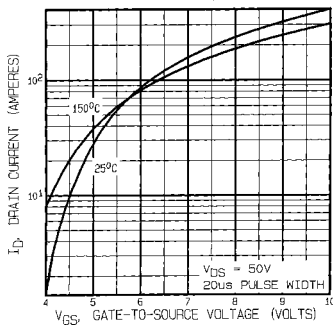


Fig 3. Typical Transfer Characteristics

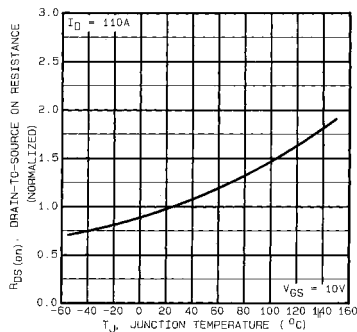


Fig 4. Normalized On-Resistance Vs.
Temperature

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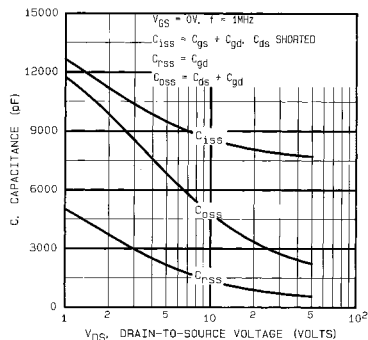


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

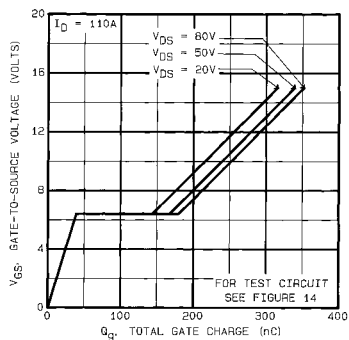


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

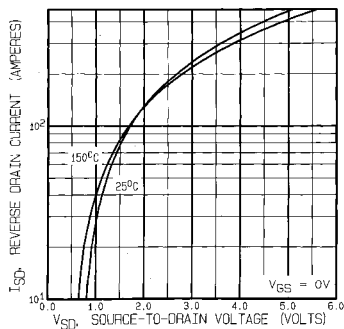


Fig 7. Typical Source-Drain Diode Forward Voltage

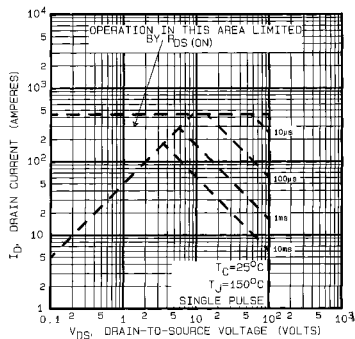


Fig 8. Maximum Safe Operating Area

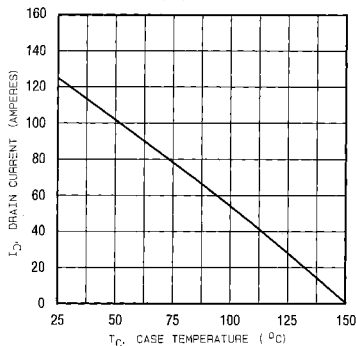


Fig 9. Maximum Drain Current Vs. Case Temperature

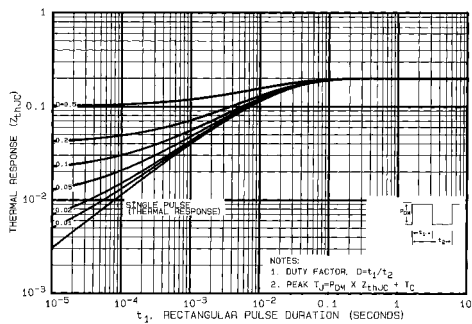


Fig 10. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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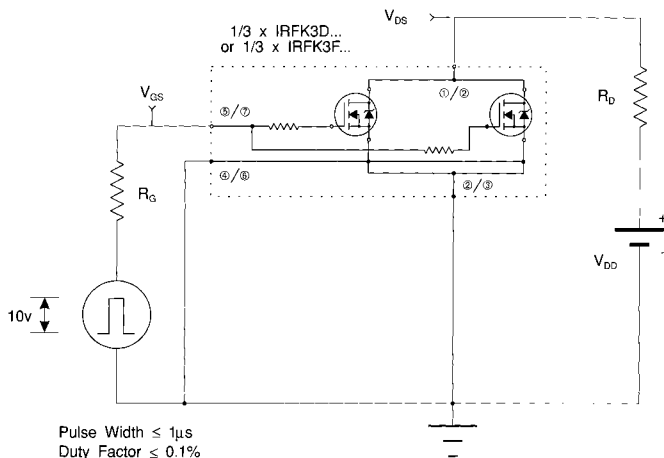


Fig 11a. Switching Time Test Circuit

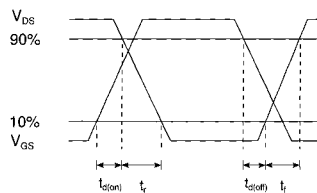
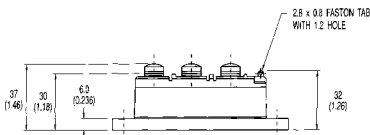
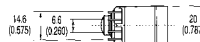
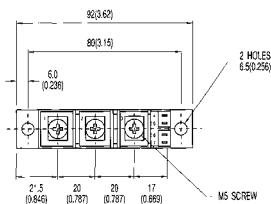
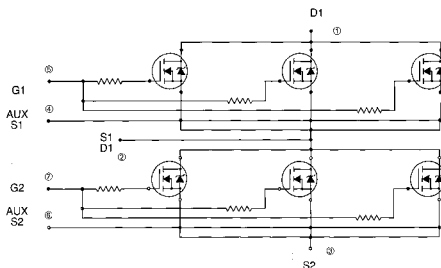


Fig 11b. Switching Time Waveforms



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Circuit Configuration and Outline



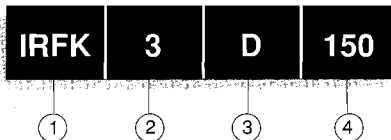
NOTE:
DEVICE IS SUPPLIED WITH
AUXILIARY LEADS 200(7.87) LONG

All dimensions in millimetres (inches)

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Part Numbering



1. - HEX-pak Module.
2. - Number of arms of bridge.
3. - D - Fast switching.
- F - Oscillation resistant for sensitive applications.
4. - Voltage code:-

054	- 60V
150	- 100V
250	- 200V
350	- 400V
450	- 500V
C50	- 600V

WORLD HEADQUARTERS: 233 Kansas St., **EL SEGUNDO**, California 90245, USA. Tel:(213) 772-2000. Tlx:654464. Fax:(213) 772-9028
EUROPEAN HEADQUARTERS: Hurst Green, **OXTED**, Surrey RH8 9BB, UK. Tel:(0883) 713215. Tlx:95219. Fax:(0883) 714234.

CANADA: 101 Bentley St. Markham, **ONTARIO** L3R 3L1. Tel:(416) 475-1897. Tlx:06-966-550. Fax:(416) 475-8801
CZECHOSLOVAKIA: Macurova 19/1565, Box 30, 149 00 **PRAGUE**. Tel:(2) 792 6831. Fax:(2) 792 6831.
DENMARK: P.O. Box 70, Kroghsvej 51, DK-2880 **BAGSVAERD**. Tel: (45) 44 37 71 50. Fax (45) 44 37 71 52.
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GERMANY: Saalburgstr. 157, D-6380 **BAD HOMBURG**. Tel:(61)72 37066. Tlx:410404. Fax:(61)72 37055.
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ITALY: Via Liguria 49, 10071 Borgaro, **TORINO**. Tel:(011)470 14 84. Tlx:221257. Fax:(011)470 42 30.
JAPAN: Via Zucca 8, 20017 Rho **MILANO**. Tel:(02)93 50 36 50. Fax:(02)93 50 36 55.
INDIA: 31 Greenacre, 5 Union Park, Khar (W), **BOMBAY** 400 052. Tel:(022)535026/533779/540242. Tlx:011-71481.
K & H Bldg. 2F, 3-30-4 Nishi-Ikebukuro, Toshima-ku, TOKYO, Japan 171. Tel:(03)983 0641. Fax:(03)983 0642.
SINGAPORE: HEX 10-01 Fortune Centre, 190 Middle Road, **SINGAPORE** 0718. Tel:(65)336 3322/337 4695/336 6296. Fax: (65)337 4692.
SWEDEN: Box. 56, S-162 12 Vällingby 1, **STOCKHOLM**. Tel:(08)870035. Fax:(08)874242.
SWITZERLAND: CH-8032 **ZURICH**, Kirchenweg 5. Tel:(01)386 6702/8596. Fax:(01)383 5108/2379.
U.S.A.:
Central Zone: 2401 Plum Grove Road, Suite 111, **PALATINE**, IL60067. Tel:(312)397-0002. Fax:(312)397-0114.
Eastern Zone: 71 Grand Avenue, **PALISADES PARK**, NJ07650. Tel:(201)943-4554. Fax:(201)943-5754.
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In the interest of product improvement INTERNATIONAL RECTIFIER reserves the right to change specifications at any time without notice.

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